

# HS25N06DA N沟道60V,MOSFET

产品名称	HS25N06DA N沟道60V,MOSFET
公司名称	深圳市硕实科技有限公司
价格	.00/个
规格参数	HS:HOMSEM HS25N06:HS25N06DA 中国:中国
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## 产品详情

深圳市硕实科技有限公司供应原装HOMSEMI MOSFET HS25N06DA  
TO252封装如有需要可致电联系0755-83040406

### Description

The HS25N06DA is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application.

Features VDS 60V RDS(on) Max. 35mΩ ID 25A High density cell design for ultra low RDS(on) Excellent package for good heat dissipation Pin configuration Order Number Package HS25N06DA TO-252

Maximum Ratings (Tc = 25°C unless otherwise noted\*)

Parameter Symbol Ratings Units  
Drain-Source Voltage VDSS 60 V  
Gate-Source Voltage VGSS ± 20 V  
Continuous Drain Current Tc=25°C ID 25\* A  
Drain Current ATc=100°C 14\* A  
Pulsed Drain Current IDM 60 A  
Power Dissipation Tc=25°C PD 45 W  
Derate above 25°C 0.3 Single pulse avalanche energy (note 1) EAS 72  
Operating Junction and Storage Temperature Range TJ, Tstg -55~+175°C  
\* Drain current limited by maximum junction temperature.  
1 : EAS condition: L=0.5mH, VDD=30V, RG=25Ω, TJ=25°C  
Thermal Characteristics  
Parameter Symbol Ratings  
Units Thermal resistance, case to sink typ. RthCS 0.5°C/W  
Thermal resistance junction to case. RthJC 3.3°C/W  
Thermal resistance junction to ambient. RthJA 110°C/W

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